



STP30NM50N Information



For Reference Only

Part Number STP30NM50N
Manufacturer STMicroelectronics

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 500V 27A TO-220

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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STP30NM50N Specifications

Manufacturer Part Number STP30NM50N Manufacturer STMicroelectronics Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series MDmesh? II FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 27A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 94nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2740pF @ 50V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 190W (Tc) Rds On (Max) @ Id, Vgs 115 mOhm @ 13.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Report errors?		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series MDmesh? II FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 27A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 94nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2740pF @ 50V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 190W (Tc) Rds On (Max) @ Id, Vgs 115 mOhm @ 13.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3	Manufacturer Part Number	STP30NM50N
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C27A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs94nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2740pF @ 50VVgs (Max)±25VFET Feature-Power Dissipation (Max)190W (Tc)Rds On (Max) @ Id, Vgs115 mOhm @ 13.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C27A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs94nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2740pF @ 50VVgs (Max)±25VFET Feature-Power Dissipation (Max)190W (Tc)Rds On (Max) @ Id, Vgs115 mOhm @ 13.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3	Series	MDmesh? II
Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C27A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs94nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2740pF @ 50VVgs (Max)±25VFET Feature-Power Dissipation (Max)190W (Tc)Rds On (Max) @ Id, Vgs115 mOhm @ 13.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 115 mOhm @ 13.5A, 10V Operating Temperature Mounting Type Through Hole Supplier Device Package Package / Case 27A (Tc) 4V @ 250μA 2740pF @ 50V 2740pF @ 50V	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs94nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2740pF @ 50VVgs (Max)±25VFET Feature-Power Dissipation (Max)190W (Tc)Rds On (Max) @ Id, Vgs115 mOhm @ 13.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3	Drain to Source Voltage (Vdss)	500V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 115 mOhm @ 13.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3	Current - Continuous Drain (Id) @ 25°C	27A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case 94nC @ 10V 2740pF @ 50V 2740pF @ 50V 190W (Tc) 190W (Tc) 190W (Tc) 115 mOhm @ 13.5A, 10V Through Hole Through Hole	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) EET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 115 mOhm @ 13.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±25VFET Feature-Power Dissipation (Max)190W (Tc)Rds On (Max) @ Id, Vgs115 mOhm @ 13.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	94nC @ 10V
FET Feature - Power Dissipation (Max) 190W (Tc) Rds On (Max) @ Id, Vgs 115 mOhm @ 13.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	2740pF @ 50V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 115 mOhm @ 13.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3	Vgs (Max)	±25V
Rds On (Max) @ Id, Vgs115 mOhm @ 13.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3	FET Feature	-
Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3	Power Dissipation (Max)	190W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	115 mOhm @ 13.5A, 10V
Supplier Device Package TO-220-3 Package / Case TO-220-3	Operating Temperature	150°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220-3
Report errors?	Package / Case	TO-220-3
Tr		Report errors?

STP30NM50N Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

STP30NM50N Payment Methods



















STP30NM50N Shipping Methods













If you have any question about STP30NM50N, please do not hesitate to contact us!

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